

ABSTRACT

A process to deposit a thin film by chemical vapor deposition includes evacuating a chamber of gases; exposing a device to a gaseous first reactant, wherein the first reactant deposits on the device to form the thin film having a plurality of monolayers in thickness; evacuating the chamber of gases; exposing the device, coated with the first reactant, to a gaseous second reactant under a plasma treatment, wherein the thin film is treated by the first reactant; and repeating the previous steps.